

RF Power Field Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

Designed for PCN and PCS base station applications with frequencies from 1000 to 2600 MHz. Suitable for FM, TDMA, CDMA, and multicarrier amplifier applications. To be used in Class A and Class AB for PCN-PCS/cellular radio and wireless local loop.

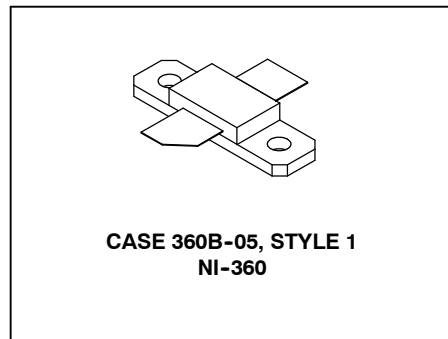
- Specified Two-Tone Performance @ 2000 MHz, 26 Volts
 - Output Power = 30 Watts PEP
 - Power Gain = 9 dB
 - Efficiency = 30%
 - Intermodulation Distortion = -29 dBc
- Typical Single-Tone Performance at 2000 MHz, 26 Volts
 - Output Power = 30 Watts CW
 - Power Gain = 9.5 dB
 - Efficiency = 45%
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 2000 MHz, 30 Watts CW Output Power

Features

- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Low Gold Plating Thickness on Leads. L Suffix Indicates 40μ" Nominal.
- RoHS Compliant
- In Tape and Reel. R1 Suffix = 500 Units per 32 mm, 13 inch Reel.

MRF284LR1

**2000 MHz, 30 W, 26 V
 LATERAL N-CHANNEL
 BROADBAND
 RF POWER MOSFET**



LIFETIME BUY

LAST ORDER 3 OCT 08 LAST SHIP 14 MAY 09

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V _{GS}	±20	Vdc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	87.5 0.5	W W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Case Operating Temperature	T _C	150	°C
Operating Junction Temperature	T _J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	R _{θJC}	2.0	°C/W

Table 3. Electrical Characteristics (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage (V _{GS} = 0, I _D = 10 μAdc)	V _{(BR)DSS}	65	—	—	Vdc
Zero Gate Voltage Drain Current (V _{DS} = 20 Vdc, V _{GS} = 0)	I _{DSS}	—	—	1.0	μAdc
Gate-Source Leakage Current (V _{GS} = 20 Vdc, V _{DS} = 0)	I _{GSS}	—	—	10	μAdc

(continued)

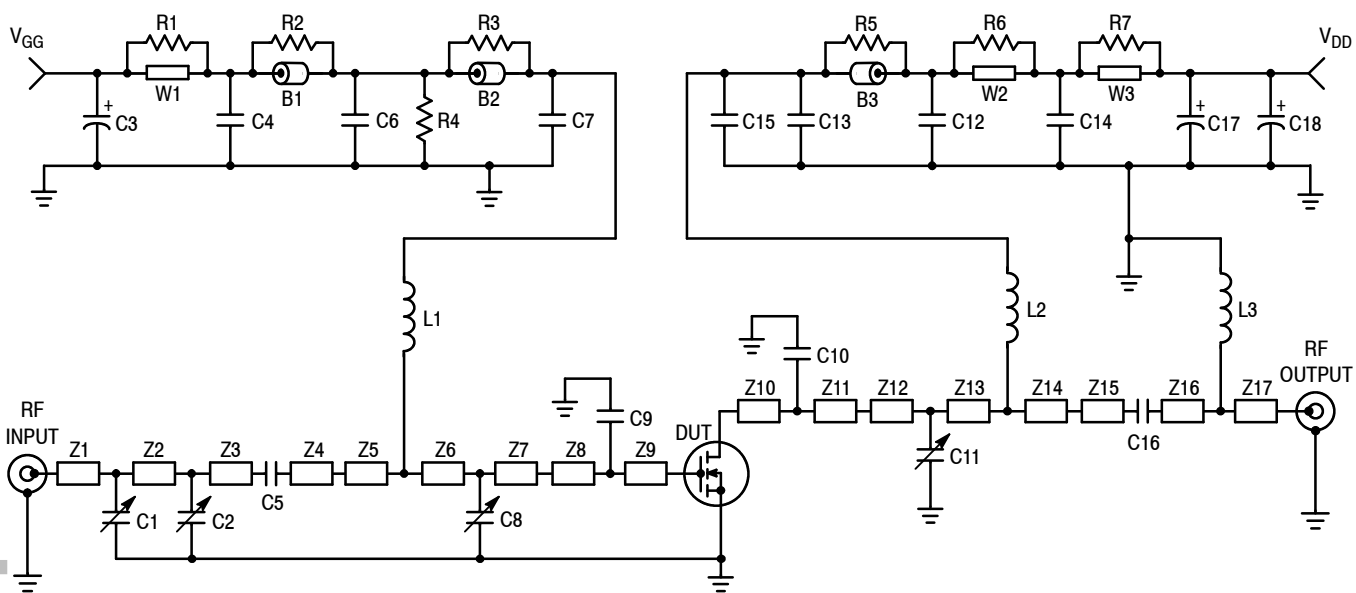
NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

Table 3. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 150\ \mu\text{Adc}$)	$V_{GS(th)}$	2.0	3.0	4.0	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 200\ \text{mAdc}$)	$V_{GS(q)}$	3.0	4.0	5.0	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1.0\ \text{Adc}$)	$V_{DS(on)}$	—	0.3	0.6	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 1.0\ \text{Adc}$)	g_{fs}	—	1.5	—	S
Dynamic Characteristics					
Input Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{iss}	—	43	—	pF
Output Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{oss}	—	23	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{rss}	—	1.4	—	pF
Functional Tests (in Freescale Test Fixture, 50 ohm system)					
Common-Source Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 30\ \text{W}$, $I_{DQ} = 200\ \text{mA}$, $f_1 = 2000.0\ \text{MHz}$, $f_2 = 2000.1\ \text{MHz}$)	G_{ps}	9	10.5	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 30\ \text{W}$, $I_{DQ} = 200\ \text{mA}$, $f_1 = 2000.0\ \text{MHz}$, $f_2 = 2000.1\ \text{MHz}$)	η	30	35	—	%
Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 30\ \text{W}$, $I_{DQ} = 200\ \text{mA}$, $f_1 = 2000.0\ \text{MHz}$, $f_2 = 2000.1\ \text{MHz}$)	IMD	—	-32	-29	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 30\ \text{W}$, $I_{DQ} = 200\ \text{mA}$, $f_1 = 2000.0\ \text{MHz}$, $f_2 = 2000.1\ \text{MHz}$)	IRL	—	-15	-9	dB
Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 30\ \text{W CW}$, $I_{DQ} = 200\ \text{mA}$, $f_1 = 2000.0\ \text{MHz}$)	G_{ps}	8.5	9.5	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 30\ \text{W CW}$, $I_{DQ} = 200\ \text{mA}$, $f_1 = 2000.0\ \text{MHz}$)	η	35	45	—	%

LIFETIME BUY

LAST ORDER 3 OCT 08 LAST SHIP 14 MAY 09

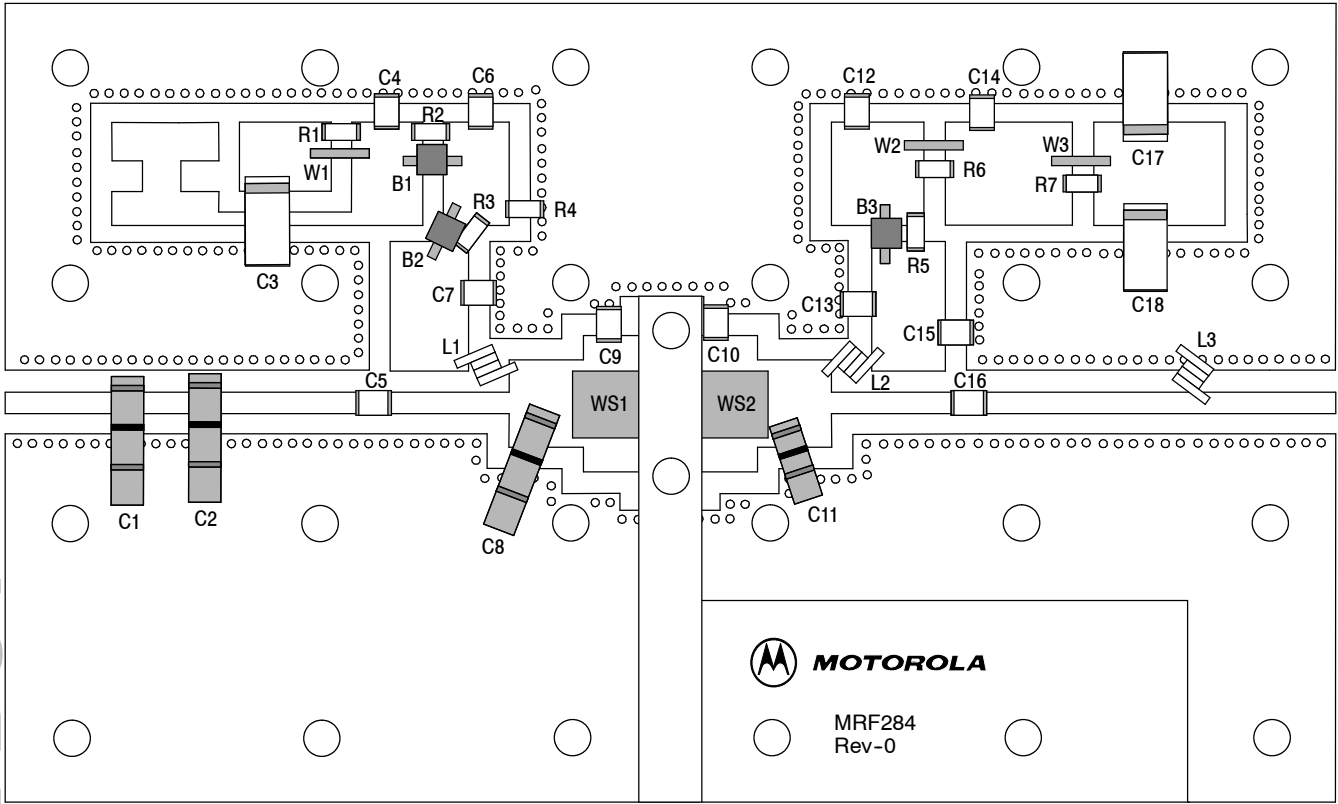


Z1	0.530" x 0.080" Microstrip	Z10	0.050" x 0.515" Microstrip
Z2	0.255" x 0.080" Microstrip	Z11	0.155" x 0.515" Microstrip
Z3	0.600" x 0.080" Microstrip	Z12	0.120" x 0.325" Microstrip
Z4	0.525" x 0.080" Microstrip	Z13	0.150" x 0.325" Microstrip
Z5	0.015" x 0.325" Microstrip	Z14	0.010" x 0.325" Microstrip
Z6	0.085" x 0.325" Microstrip	Z15	0.505" x 0.080" Microstrip
Z7	0.165" x 0.325" Microstrip	Z16	0.865" x 0.080" Microstrip
Z8	0.110" x 0.515" Microstrip	Z17	0.525" x 0.080" Microstrip
Z9	0.095" x 0.515" Microstrip	PCB	Arlon GX0300-55-22, 0.030", $\epsilon_r = 2.55$

Figure 1. 1930-2000 MHz Broadband Test Circuit Schematic

Table 4. 1930-2000 MHz Broadband Test Circuit Component Designations and Values

Designators	Description
B1 - B3	Ferrite Beads, Round, Ferroxcube #56-590-65-3B
C1, C2, C8	0.8-8.0 pF Gigatrim Variable Capacitors, Johanson #27291SL
C3, C17	22 μ F, 35 V Tantalum Surface Mount Chip Capacitors, Kemet #T491X226K035AT
C4, C14	0.1 μ F Chip Capacitors, Kemet #CDR33BX104AKYS
C5	220 pF Chip Capacitor, ATC #100B221KT500XT
C6, C12	1000 pF Chip Capacitors, ATC #100B102JT50XT
C7, C13	5.1 pF Chip Capacitors, ATC #100B5R1CT500XT
C9	1.2 pF Chip Capacitor, ATC #100B1R2CT500XT
C10	2.7 pF Chip Capacitor, ATC #100B2R7CT500XT
C11	0.6-4.5 pF Gigatrim Variable Capacitors, Johanson #27271SL
C15, C16	200 pF Chip Capacitors, ATC #100B201KT500XT
C18	10 μ F, 35 V Tantalum Surface Mount Chip Capacitor, Kemet #T495X106K035AT
L1, L2	4 Turns, #24 AWG, 0.120" OD, 0.140" Long, (12.5 nH), Coilcraft #A04T-5
L3	2 Turns, #24 AWG, 0.120" OD, 0.140" Long, (5.0 nH), Coilcraft #A02T-5
R1, R2, R3, R5, R6, R7	12 Ω , 1/4 W Chip Resistors, 0.08" x 0.13", Vishay #CRCW120612R0FKEA
R4	560 k Ω , 1/4 W Chip Resistor, 0.08" x 0.13", Vishay #CRCW12065600FKEA



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. 1930-2000 MHz Broadband Test Circuit Component Layout

LIFETIME BUY

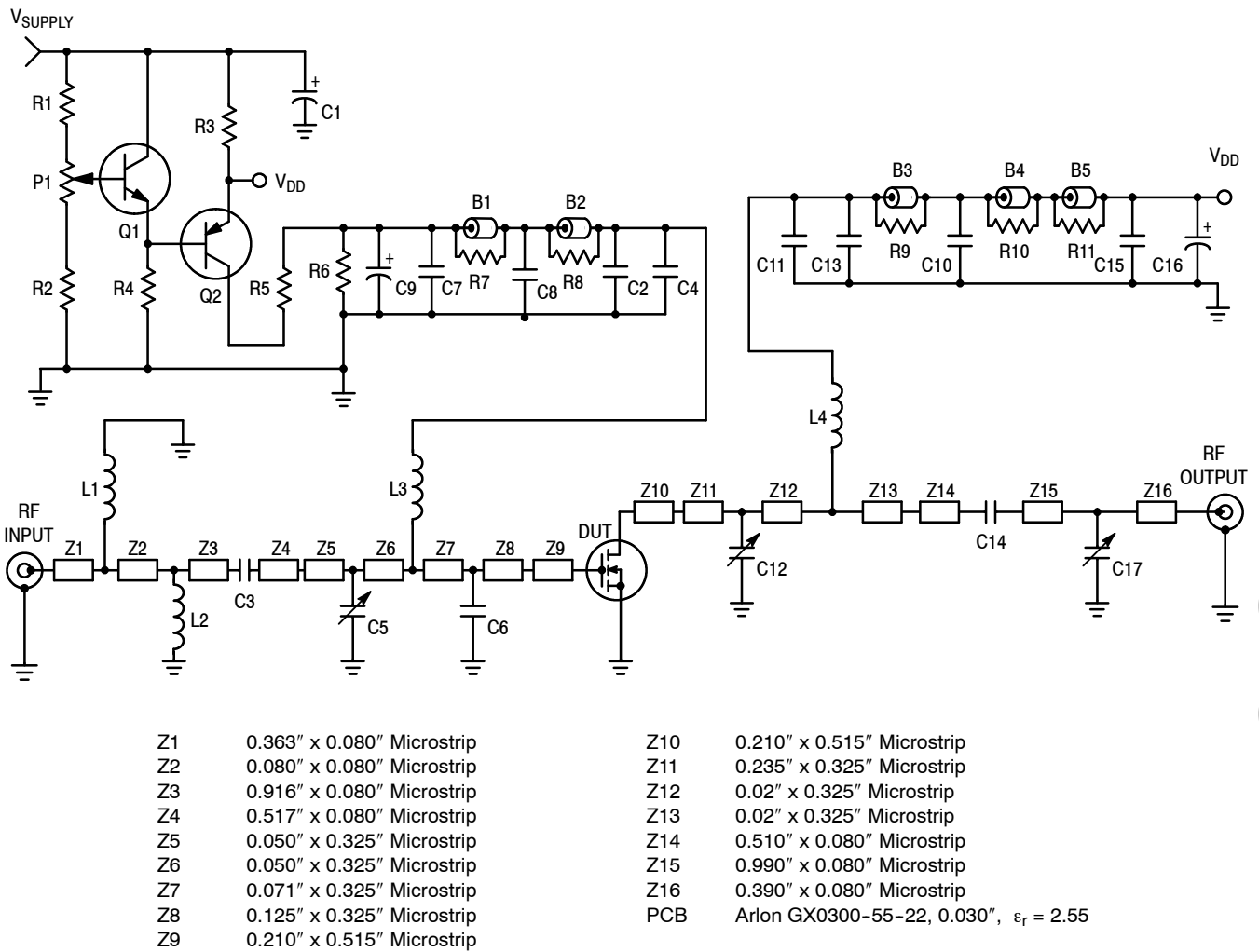


Figure 3. 2000 MHz Class A Test Circuit Schematic

LAST ORDER 3 OCT 08 LAST SHIP 14 MAY 09

Table 5. 2000 MHz Class A Test Circuit Component Designations and Values

Designators	Description
B1 - B5	Ferrite Beads, Round, Ferroxcube # 56-590-65-3B
C1, C9, C16	100 μ F, 50 V Electrolytic Capacitors, Multicomp #MCHT101M1HB-1017-RH
C2, C13	51 pF Chip Capacitors, ATC #100B510JT500XT
C3, C14	10 pF Chip Capacitors, ATC #100B100JT500XT
C4, C11	12 pF Chip Capacitors, ATC #100B120JT500XT
C5	0.8 - 8.0 pF Variable Capacitor, Johansen Gigatrim #27291SL
C6	4.7 pF Chip Capacitor, ATC #100B4R7CT500XT
C7, C15	91 pF Chip Capacitors, ATC #100B910KT500XT
C8	1000 pF Chip Capacitor, ATC #100B102JT500XT
C10	0.1 μ F Chip Capacitor, Kemet #CDR33BX104AKYS
C12, C17	0.6 - 4.5 pF Variable Capacitors, Johansen Gigatrim #27271SL
L1	4 Turns, #27 AWG, 0.087" OD, 0.050" ID, 0.069" Long, 10 nH
L2	5 Turns, #24 AWG, 0.083" OD, 0.040" ID, 0.128" Long, 12.5 nH
L3, L4	9 Turns, #26 AWG, 0.080" OD, 0.046" ID, 0.170" Long, 30.8 nH
P1	1000 Ω Potentiometer, 1/2 W, 10 Turns, Bourns #3224W
Q1	Transistor, NPN, #MJD31, Case 369A-10, On Semi #MJD31T4G
Q2	Transistor, PNP, #MJD32, Case 369A-10, On Semi #MJD32T4G
R1	360 Ω , 1/4 W Fixed Film Chip Resistor, Vishay #CRCW12063600FKEA
R2	2 x 12 k Ω , 1/4 W Fixed Film Chip Resistor, Vishay #CRCW120612R0FKEA
R3	1 Ω , Wirewound, 5 W, 3% Resistor, Dale # RE60G1R00C02
R4	4 x 6.8 k Ω , 1/4 W Fixed Film Chip Resistor, Vishay #CRCW12066801FKEA
R5	2 x 1500 Ω , 1/4 W Fixed Film Chip Resistor, Vishay #CRCW12061501FKEA
R6	270 Ω , 1/4 W Fixed Film Chip Resistor, Vishay #CRCW12062700FKEA
R7 - R11	12 Ω , 1/4 W Fixed Film Chip Resistors, Vishay #CRCW120612R0FKEA

LIFETIME BUY

LAST ORDER 3 OCT 08 LAST SHIP 14 MAY 09

TYPICAL CHARACTERISTICS

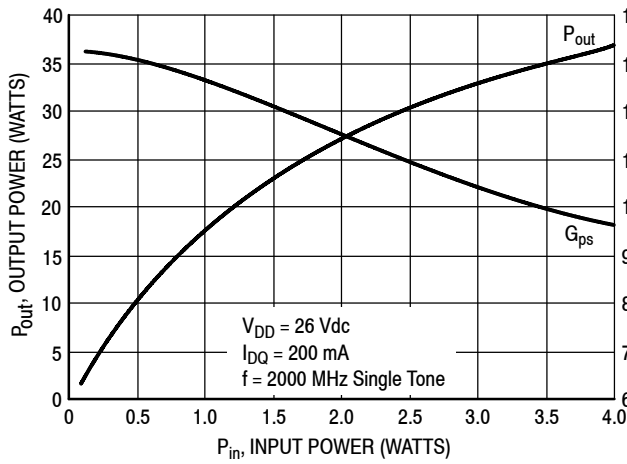


Figure 4. Output Power & Power Gain versus Input Power

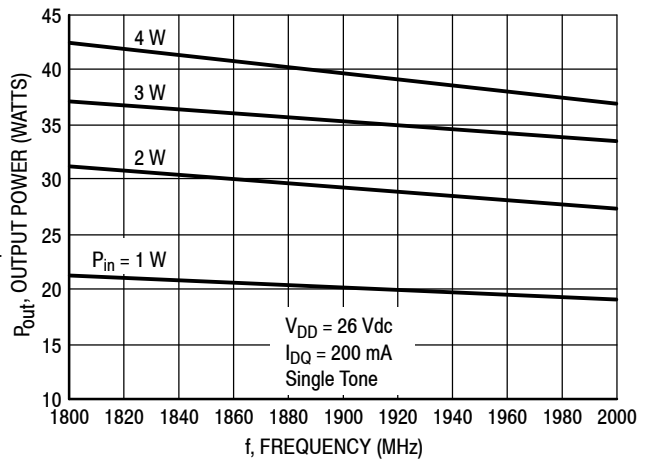


Figure 5. Output Power versus Frequency

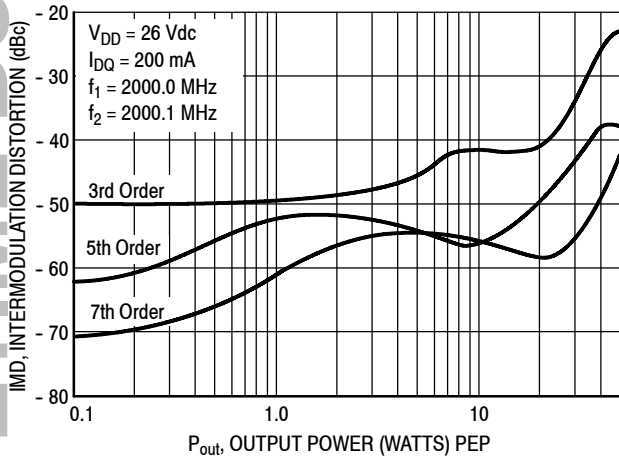


Figure 6. Intermodulation Distortion Products versus Output Power

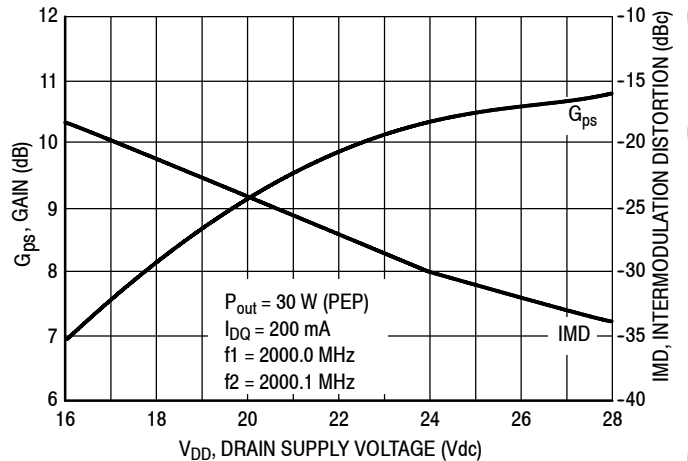


Figure 7. Power Gain and Intermodulation Distortion versus Supply Voltage

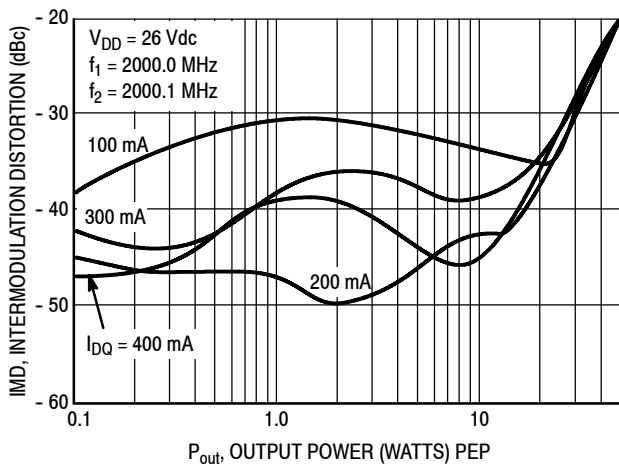


Figure 8. Intermodulation Distortion versus Output Power

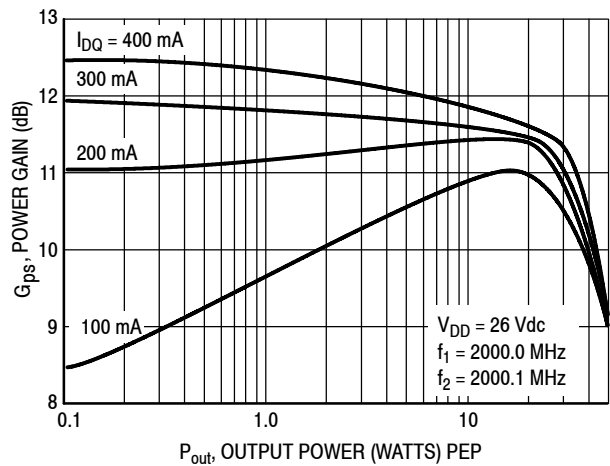


Figure 9. Power Gain versus Output Power

LIFETIME BUY

LAST ORDER 3 OCT 08 LAST SHIP 14 MAY 09

TYPICAL CHARACTERISTICS

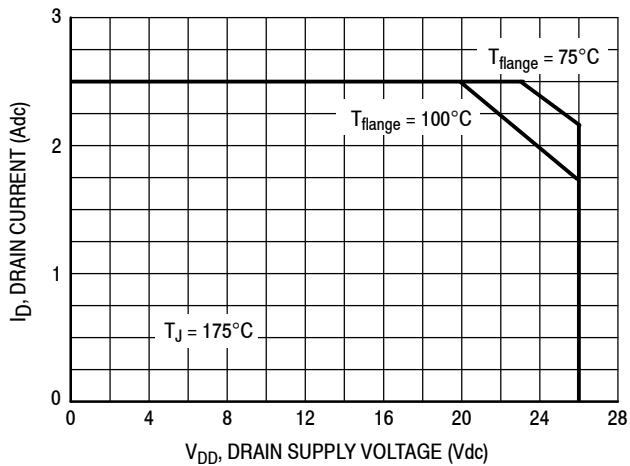


Figure 10. DC Safe Operating Area

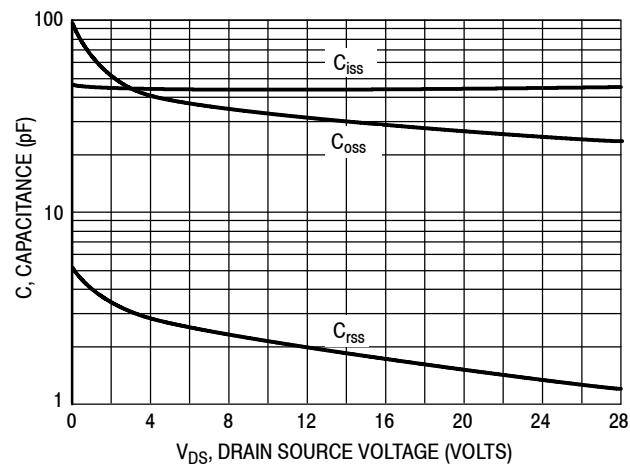


Figure 11. Capacitance versus Drain Source Voltage

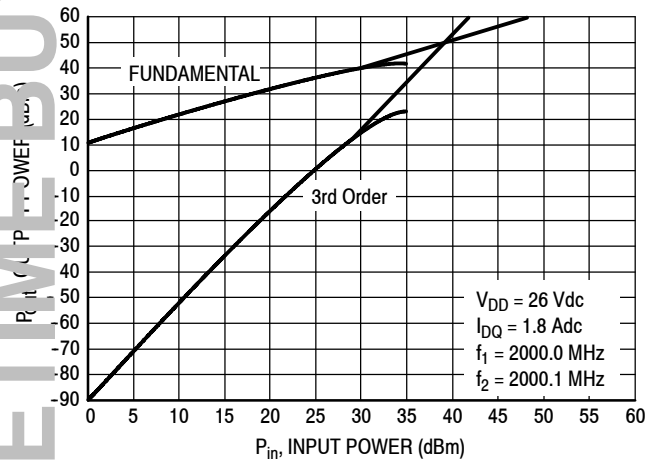


Figure 12. Class A Third Order Intercept Point

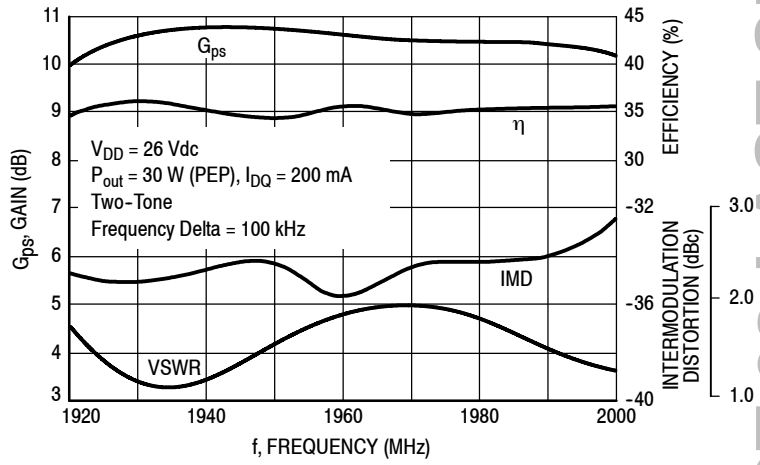
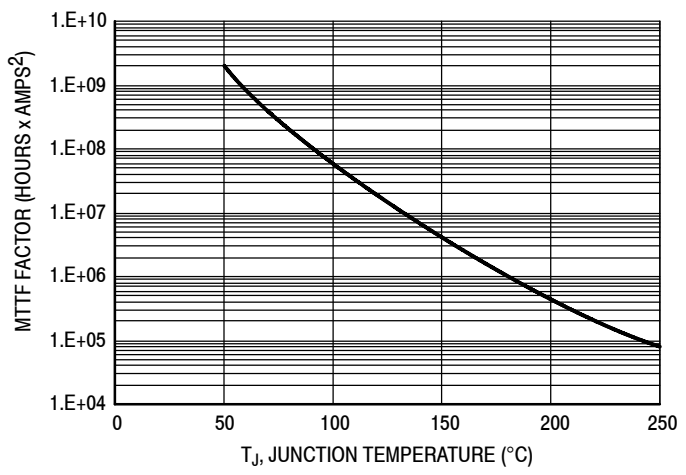


Figure 13. 1920-2000 MHz Broadband Circuit Performance

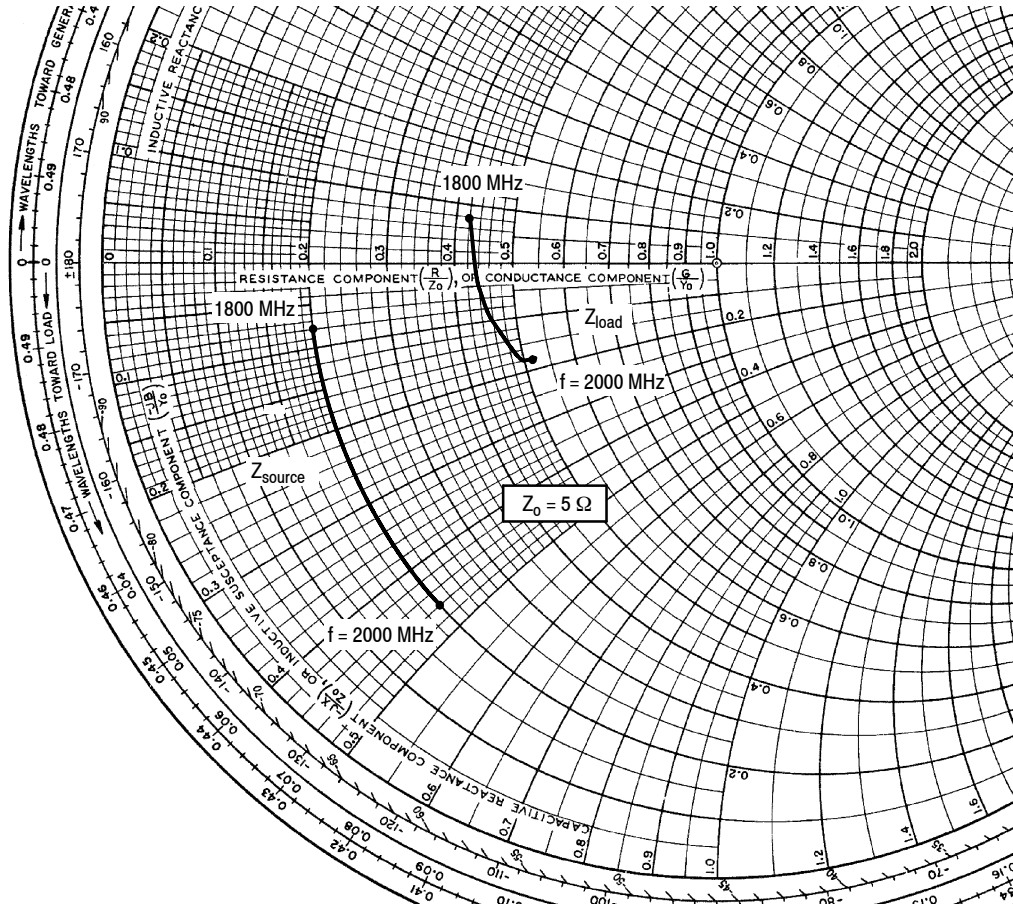


This graph displays calculated MTTF in hours x ampere² drain current. Life tests at elevated temperature have correlated to better than ±10% of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 14. MTTF Factor versus Junction Temperature

LIFETIME BUY

LAST ORDER 3 OCT 08 LAST SHIP 14 MAY 09



$V_{CC} = 26\text{ V}$, $I_{DQ} = 200\text{ mA}$, $P_{out} = 15\text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
1800	$1.0 - j0.4$	$2.1 + j0.4$
1860	$1.0 - j0.8$	$2.2 - j0.2$
1900	$1.0 - j1.1$	$2.3 - j0.5$
1960	$1.0 - j1.4$	$2.5 - j0.9$
2000	$1.0 - j2.3$	$2.6 - j0.92$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

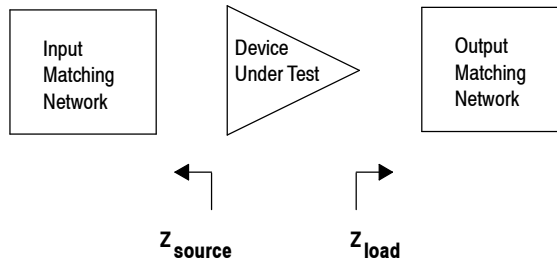
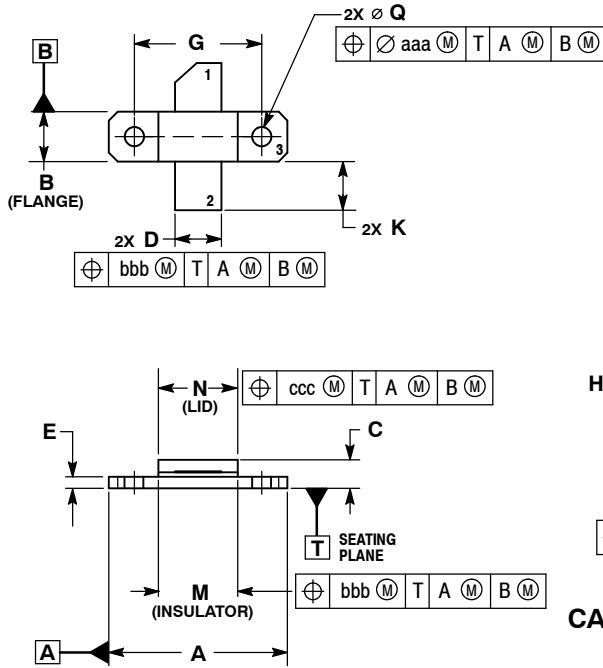


Figure 15. Series Equivalent Source and Load Impedence

PACKAGE DIMENSIONS



NOTES:

1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.795	0.805	20.19	20.45
B	0.225	0.235	5.72	5.97
C	0.125	0.175	3.18	4.45
D	0.210	0.220	5.33	5.59
E	0.055	0.065	1.40	1.65
F	0.004	0.006	0.10	0.15
G	0.562 BSC		14.28 BSC	
H	0.077	0.087	1.96	2.21
K	0.220	0.250	5.59	6.35
M	0.355	0.365	9.02	9.27
N	0.357	0.363	9.07	9.22
Q	0.125	0.135	3.18	3.43
R	0.227	0.233	5.77	5.92
S	0.225	0.235	5.72	5.97
aaa	0.005 REF		0.13 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	

STYLE 1:

- PIN 1. DRAIN
- GATE
- SOURCE

CASE 360B-05
ISSUE G
NI-360
MRF284LR1

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
19	Oct. 2008	<ul style="list-style-type: none"> • Data sheet revised to reflect part status change, p. 1, including use of applicable overlay. • Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN12779, p. 2 • Updated Part Numbers in Tables 4 and 5, Component Designations and Values, to RoHS compliant part numbers, p. 3, 6 • Added Product Documentation and Revision History, p. 11

How to Reach Us:

Home Page:

www.freescale.com

Web Support:

<http://www.freescale.com/support>

USA/Europe or Locations Not Listed:

Freescale Semiconductor, Inc.
 Technical Information Center, EL516
 2100 East Elliot Road
 Tempe, Arizona 85284
 1-800-521-6274 or +1-480-768-2130
www.freescale.com/support

Europe, Middle East, and Africa:

Freescale Halbleiter Deutschland GmbH
 Technical Information Center
 Schatzbogen 7
 81829 Muenchen, Germany
 +44 1296 380 456 (English)
 +46 8 52200080 (English)
 +49 89 92103 559 (German)
 +33 1 69 35 48 48 (French)
www.freescale.com/support

Japan:

Freescale Semiconductor Japan Ltd.
 Headquarters
 ARCO Tower 15F
 1-8-1, Shimo-Meguro, Meguro-ku,
 Tokyo 153-0064
 Japan
 0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:

Freescale Semiconductor China Ltd.
 Exchange Building 23F
 No. 118 Jianguo Road
 Chaoyang District
 Beijing 100022
 China
 +86 10 5879 8000
support.asia@freescale.com

For Literature Requests Only:

Freescale Semiconductor Literature Distribution Center
 P.O. Box 5405
 Denver, Colorado 80217
 1-800-441-2447 or +1-303-675-2140
 Fax: +1-303-675-2150
LDCForFreescaleSemiconductor@hibbertgroup.com

Information in this document is provided solely to enable system and software implementers to use Freescale Semiconductor products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits or integrated circuits based on the information in this document.

Freescale Semiconductor reserves the right to make changes without further notice to any products herein. Freescale Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Freescale Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in Freescale Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals", must be validated for each customer application by customer's technical experts. Freescale Semiconductor does not convey any license under its patent rights nor the rights of others. Freescale Semiconductor products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Freescale Semiconductor product could create a situation where personal injury or death may occur. Should Buyer purchase or use Freescale Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold Freescale Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Freescale Semiconductor was negligent regarding the design or manufacture of the part.

Freescale™ and the Freescale logo are trademarks of Freescale Semiconductor, Inc. All other product or service names are the property of their respective owners.
 © Freescale Semiconductor, Inc. 2008. All rights reserved.